

View Online at <https://aerobasegroup.com/nsn/5961-01-594-7973>

Function For Which Designed:

Switching

Mounting Facility Quantity:

2

Mounting Method:

Unthreaded hole

Semiconductor Material:

Silicon

Power Rating Per Characteristic:

150.0 watts total device dissipation

Special Features:

Single pulse avalanche energy related; soa is power dissipation limited; nanosecond switching speeds; linear transfer characteristics; high input impedance; -25 to -100v; p-channel enhancement mode gate power field effect transistor

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fig:

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